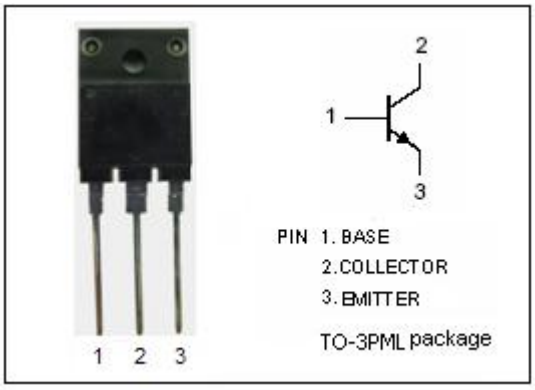
isc Silicon NPN Power Transistors — 2SC4941

DESCRIPTION

- Collector-Emitter Sustaining Voltage-
  : $V_{CEO(SUS)}$= 800V(Min)
- Fast Switching speed
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



APPLICATIONS

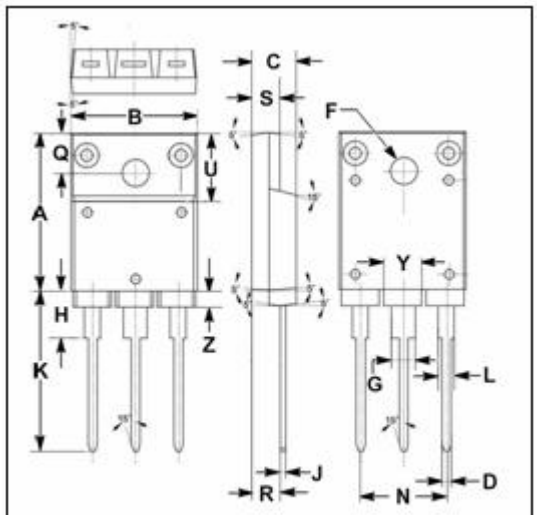
- Color TV horizontal deflection output applications
- Color display horizontal deflection output applications

ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	1500	V
V_{CEO}	Collector-Emitter Voltage	800	V
V_{EBO}	Emitter-Base Voltage	7	V
I_C	Collector Current-Continuous	6	A
I_{CP}	Collector Current-Peak	12	A
I_B	Base Current-Continuous	3	A
I_{BP}	Base Current-Peak	6	A
P_T	Total Power Dissipation @ T_C=25℃	65	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance,Junction to Case	1.92	℃/W



DIM	mm MIN	MAX
A	19.90	20.10
B	15.75	16.10
C	5.50	5.70
D	0.90	1.10
F	3.30	3.50
G	2.90	3.20
H	5.90	6.10
J	0.595	0.70
K	21.10	22.50
L	1.90	2.25
N	10.80	11.00
Q	4.90	5.10
R	3.75	3.95
S	3.20	3.60
U	9.90	10.10
Y	4.20	4.90
Z	1.90	2.10

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	I_C=50mA; I_B= 0	800			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 3A; I_B= 0.6A			0.5	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= 3A; I_B= 0.6A			1.5	V
I_{CBO}	Collector Cutoff Current	At rated Voltage			100	μA
I_{CEO}	Collector Cutoff Current	At rated Voltage			100	μA
I_{EBO}	Emitter Cutoff Current	At rated Voltage			100	μA
h_{FE-1}	DC Current Gain	I_C= 1A ; V_{CE}= 5V	15			
h_{FE-2}	DC Current Gain	I_C= 1mA ; V_{CE}= 5V	7			
f_T	Current-Gain—Bandwidth Product	I_C= 0.6A ; V_{CE}= 10V		8		MHz